Study of Workload Impact on BTI HCI Induced Aging of Digital Circuits

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Abstract— Workload characterization of digital circuits using industry standard benchmarks gives an insight into the performance and energy characteristics of processor designs. Aging studies of digital circuits due to BTI, HCI is gaining importance since a higher impact on the performance of circuits can be observed as we scale down gate dimensions. For embedded system applications, the workload may very well dictate the lifetime of a system. This article aims to study the influence of different workloads on the degradation of critical path which determines the reliability of a system. A top-down circuit activity and probability analysis is carried out leading to an accurate estimation of aging due to HCI and BTI of critical path elements at the design stage. A dedicated simulation flow has been set up, from RTL simulation down to gate level cell timing analysis mapped onto 28nm FDSOI technology from STMicroelectronics. The objective is to correlate path delay timing with aging of critical path cells. Simulation results indicate that the higher complexity of an execution program may not necessarily lead to a higher rate of degradation of the critical path considering that aging is primarily driven by the workload dependent activity and the probability of critical path combinational logic elements.

Keywords— Workload, Aging, Critical Path, Reliability

I. DESIGN AND FLOW METHODOLOGY

A. openMSP430 Architecture

The design under use is an open-source synthesizable 16 bit microcontroller core from TI MSP430 family based on Von Neumann architecture and written in Verilog HDL. The modules depicted in red in Fig 1 were observed to show the maximum activity based on RTL simulations and so they are the modules that are of interest in relation to this paper. The openMSP430 was further synthesized onto 28nm FDSOI technology.

B. Workload dependent Aging analysis Flow

Activity is defined as the average number of transitions of a net per clock period for the entire simulation cycle. Probability in this research paper refers to the probability of observing a logic 1 at a particular net per clock cycle.

Activity and probability information for all nets in the design corresponding to 10 different Benchmark programs for a full simulation run is obtained.
The critical paths with highest activity have been highlighted in the graph Fig. 3 (bottom). The cell from which the net originates is expected to see maximum HCI related degradation. The nets without activity will have a logic level of 1 or 0 associated with it and this is an indicator of possible worst case degradation due to BTI as in Fig. 3 (top).

Fig. 3. Path level activity and probability plots

B. Cell Level Analysis

The cell level analysis of the critical path provides complete data on how the individual elements in the critical path ages. In Fig. 4 (bottom), the cells most affected by HCI is identified. In Fig. 4 (top), for a different workloads, probability of the nets along the Critical Path being either 1 or 0 provides information on BTI degradation.

Higher complexity of the workload does not necessarily lead to a higher activity of all the critical paths but it has an impact on certain potential critical paths [2].

C. Timing Arc degradation

The impact of activity and probability are now reviewed at cell level. Using Design for Reliability models, it is possible to evaluate the degradation of cell for a given stimuli and mission profile. Assuming 2 years of operating conditions at Vmax, the degradation of a NAND3A is depicted in Fig. 5. At a given input slope and load, delay of rising and falling arcs are simulated. It is noticeable that degradation is a function of both the activity and probability driven respectively by HCI and BTI mechanisms. However, there is coupling between both these mechanisms, as explained in [3]. These effects are not additive but they do interact with each other. For this particular arc, an always ‘0’ at input leads to drastic cell degradation because of PMOS degradation. This gets exacerbated at high activity.

Fig. 5. Timing arcs degradation for NAND3A cell for different probability and activity

CONCLUSION

This paper discusses a flow that provides workload dependent HCI and BTI related degradation information to the designer at the very beginning of the design stage. Workload dependent activity and probability information of the critical path nets of a digital circuit is gathered. Higher the activity and probability on a certain net, higher will be degradation due to HCI and BTI respectively of cells from which the nets originate. A designer can thus improve the reliability of a hardware, by taking into account the HCI and BTI aging for a certain application during the design stage.

REFERENCES